

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK12P60W

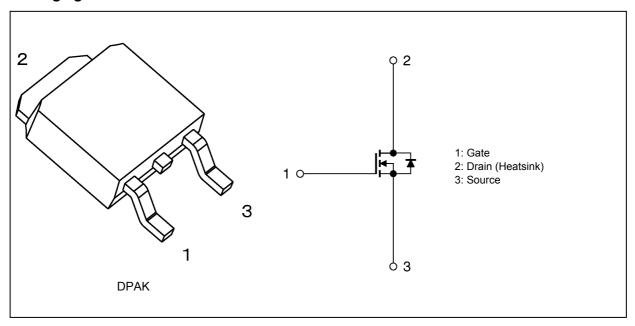
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.265 Ω (typ.) by used to Super Junction Structure: DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.7 to 3.7 V (V_{DS} = 10 V, I_D = 0.6 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics | | Symbol | Rating | Unit |
|---------------------------------------|----------|------------------|------------|------|
| Drain-source voltage | | V _{DSS} | 600 | V |
| Gate-source voltage | | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | I _D | 11.5 | Α |
| Drain current (pulsed) | (Note 1) | I _{DP} | 46.0 | |
| Power dissipation (T _c = 2 | 5°C) | P _D | 100 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 140 | mJ |
| Avalanche current | | I _{AR} | 3.0 | Α |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 11.5 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 46.0 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 1.25 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 27.2 mH, R_G = 25 Ω , I_{AR} = 3.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



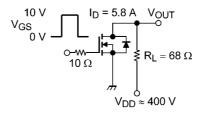
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|-------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | _ | V |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 0.6 mA | 2.7 | _ | 3.7 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 5.8 A | ı | 0.265 | 0.34 | Ω |

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz | _ | 890 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 2.8 | _ | |
| Output capacitance | C _{oss} | | _ | 23 | _ | |
| Effective output capacitance | C _{o(er)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 41 | _ | |
| Gate resistance | r _g | V _{DS} = OPEN, f = 1 MHz | _ | 6.5 | _ | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1 | _ | 23 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 45 | _ | |
| Switching time (fall time) | t _f | | _ | 5.5 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 85 | | |
| MOSFET dv/dt ruggedness | dv/dt | V _{DD} = 0 to 400 V, I _D = 5.8 A | 50 | _ | | V/ns |



 $Duty \leq 1\%, \ t_W = 10 \ \mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11.5 \text{ A}$ | 1 | 25 | 1 | nC |
| Gate-source charge 1 | Q _{gs1} | | | 5.5 | | |
| Gate-drain charge | Q_{gd} | | | 11 | | |

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage | V_{DSF} | I _{DR} = 11.5 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 5.8 A, V _{GS} = 0 V | _ | 250 | _ | ns |
| Reverse recovery charge | Q_{rr} |]-dI _{DR} /dt = 100 A/μs | _ | 2.3 | _ | μС |
| Peak reverse recovery current | I _{rr} | | _ | 20 | _ | Α |
| Diode dv/dt ruggedness | dv/dt | $I_{DR} = 5.8 \text{ A}, V_{GS} = 0 \text{ V}, V_{DD} = 400 \text{ V}$ | 15 | _ | _ | V/ns |



7. Marking

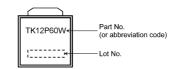


Fig. 7.1 Marking

8. Characteristics Curves (Note)

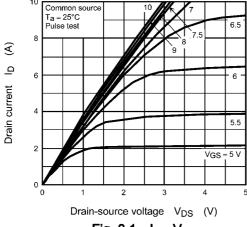
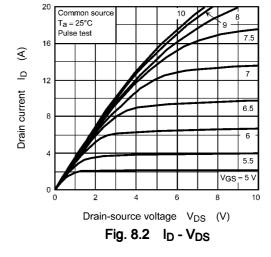


Fig. 8.1 I_D - V_{DS}



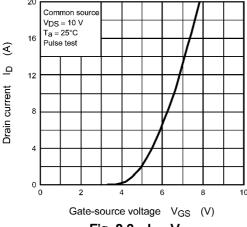


Fig. 8.3 I_D - V_{GS}

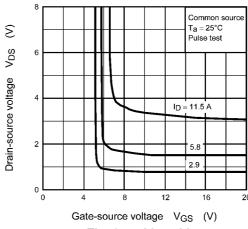
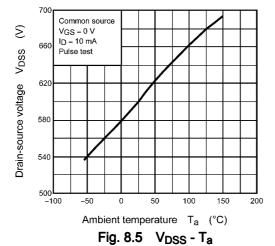


Fig. 8.4 VDS - VGS



Onin current I_D (A)

Fig. 8.6 $R_{DS(ON)}$ - I_D

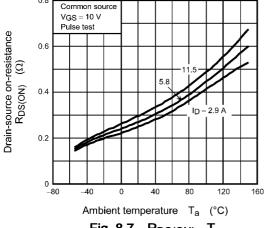


Fig. 8.7 R_{DS(ON)} - T_a

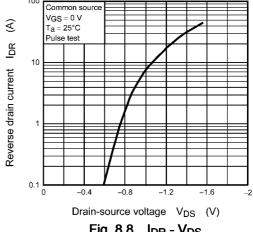


Fig. 8.8 IDR - VDS

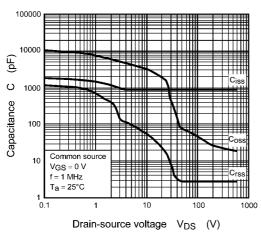


Fig. 8.9 $\,$ C - V_{DS}

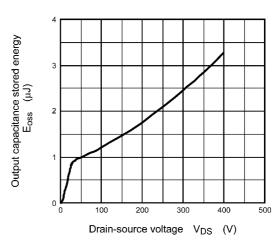


Fig. 8.10 E_{OSS} - V_{DS}

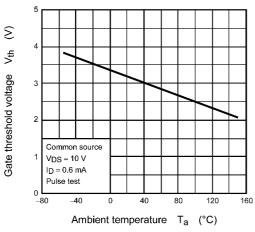


Fig. 8.11 V_{th} - T_a

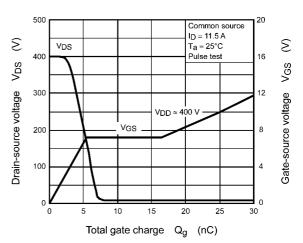


Fig. 8.12 Dynamic Input/Output Characteristics

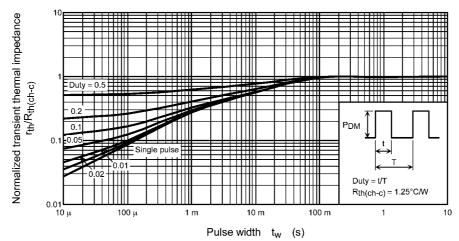


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

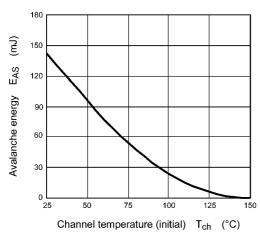


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

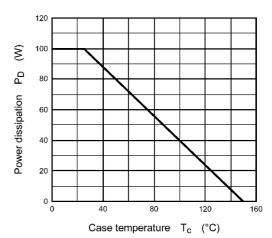
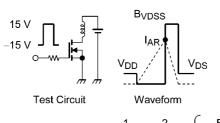


Fig. 8.15 P_D - T_c (Guaranteed Maximum)



 $R_G = 25 \Omega$, $V_{DD} = 90 V$ $E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$

Fig. 8.16 Test Circuit/Waveform

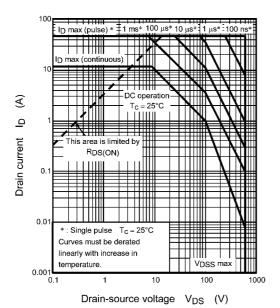
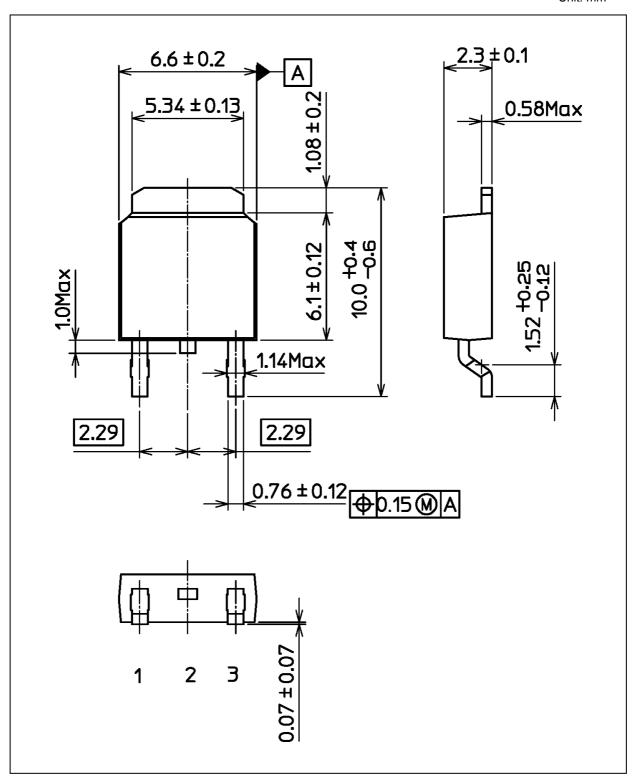


Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| | Package Name(s) |
|-----------------|-----------------|
| TOSHIBA: 2-7K1S | |
| Nickname: DPAK | |



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